



2DB1714

## LOW V<sub>CE(SAT)</sub> PNP SURFACE MOUNT TRANSISTOR

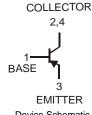
#### **Features**

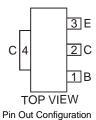
- **Epitaxial Planar Die Construction**
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Complementary NPN Type (2DD2679) Available
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

### **Mechanical Data**

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)







**Device Schematic** 

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Peak Pulse Current	I <sub>CM</sub>	-4	A
Continuous Collector Current	Ic	-2	A

#### Thermal Characteristics

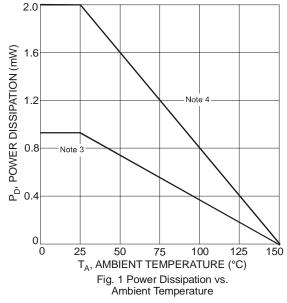
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	0.9	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	139	°C/W
Power Dissipation (Note 4) @ T <sub>A</sub> = 25°C	$P_{D}$	2	W
Thermal Resistance, Junction to Ambient Air (Note 4) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

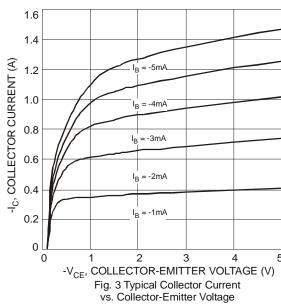
## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-30	_	_	V	$I_C = -10\mu A$ , $I_E = 0$
Collector-Emitter Breakdown Voltage (Note 5)	V <sub>(BR)CEO</sub>	-30	_	_	V	$I_C = -1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-6	_	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current	I <sub>CBO</sub>	_	_	-0.1	μΑ	$V_{CB} = -30V, I_{E} = 0$
Emitter Cut-Off Current	I <sub>EBO</sub>	_	_	-0.1	μΑ	$V_{EB} = -6V, I_C = 0$
ON CHARACTERISTICS (Note 5)						•
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	-370	mV	$I_C = -1.5A$ , $I_B = -75mA$
DC Current Gain	$h_{FE}$	270	_	680	_	$V_{CE} = -2V, I_{C} = -200 \text{mA}$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C <sub>obo</sub>	_	16	_	pF	$V_{CB} = -10V, I_E = 0,$ f = 1MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	_	200	_	MHz	$V_{CE} = -2V, I_{C} = -100mA,$ f = 100MHz

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Device mounted on FR-4 PCB with minimum recommended pad layout.
- Device mounted on FR-4 PCB with 1 inch<sup>2</sup> copper pad layout.
- Measured under pulsed conditions. Pulse width =  $300\mu s$ . Duty cycle  $\leq 2\%$ .







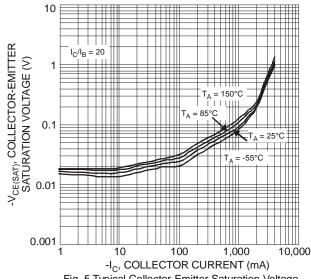
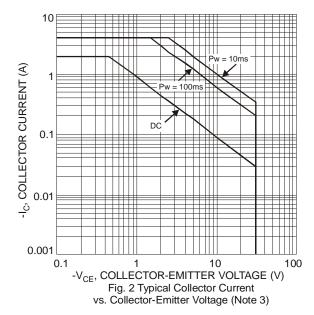


Fig. 5 Typical Collector-Emitter Saturation Voltage vs. Collector Current



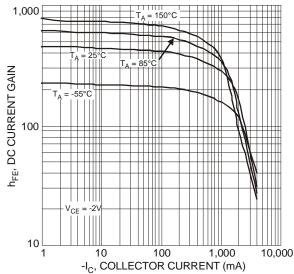


Fig. 4 Typical DC Current Gain vs. Collector Current

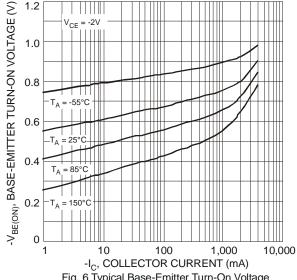
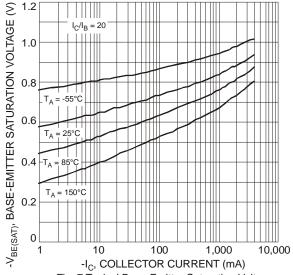
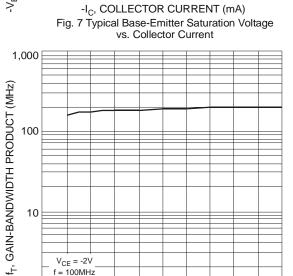


Fig. 6 Typical Base-Emitter Turn-On Voltage vs. Collector Current







 $I_{\mathbb{C}}$ , COLLECTOR CURRENT (mA) Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

70 80

30 40 50 60

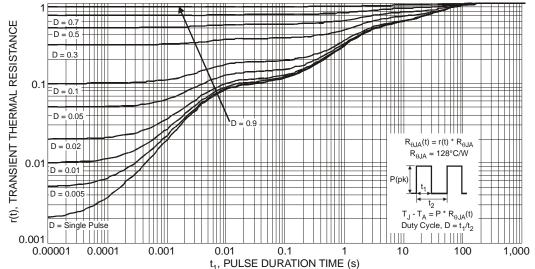


Fig. 10 Transient Thermal Response

Fig. 8 Typical Capacitance Characteristics

0 10 20

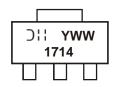


#### Ordering Information (Note 6)

Part Number	Case	Packaging
2DB1714-13	SOT89-3L	2500/Tape & Reel

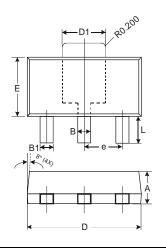
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

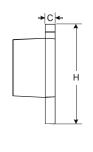
## **Marking Information**



1714 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 8 = 2008) WW = Week code 01 - 52

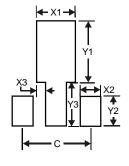
## **Package Outline Dimensions**





SOT89-3L				
Dim	Min	Max	Тур	
Α	1.40	1.60	1.50	
В	0.45	0.55	0.50	
B1	0.37	0.47	0.42	
C	0.35	0.43	0.38	
D	4.40	4.60	4.50	
D1	1.50	1.70	1.60	
Е	2.40	2.60	2.50	
е	_	_	1.50	
Н	3.95	4.25	4.10	
L	0.90	1.20	1.05	
All Dimensions in mm				

## **Suggested Pad Layout**



<b>Dimensions</b>	Value (in mm)
X1	1.7
X2	0.9
Х3	0.4
Y1	2.7
Y2	1.3
Y3	1.9
С	3.0

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